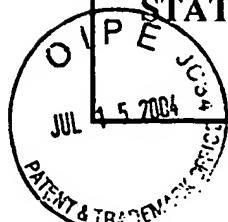


INFORMATION
DISCLOSURE
STATEMENT

Atty. Docket No.: 150.01300102	Serial No.: 10/828,686
Applicants: Vaartstra et al.	Confirmation No.: 4467
Application Filing Date: April 21, 2004	Group: 2812
Information Disclosure Statement mailed:	July 12, 2004

U.S. PATENT DOCUMENTS

Examiner Initial	Copies Enclosed	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
		5,256,244	10/26/93	Ackerman			
		5,742,322	04/21/98	Cranton et al.			
		5,908,947	06/01/99	Vaartstra			
		6,143,081	11/07/00	Shinriki et al.			
		6,203,613	03/20/01	Gates et al.			
		6,271,094	08/07/01	Boyd et al.			
		6,335,049	01/01/02	Basceri			
		6,342,445	01/29/02	Marsh			
		6,387,764	05/14/02	Curtis et al.			
W		6,730,164	05/04/04	Vaartstra et al.			

FOREIGN PATENT DOCUMENTS

Examiner Initial	Copies Enclosed	Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
W	X	0 442 704 A2	12/02/91	EP				

OTHER DOCUMENTS (Including Authors, Title, Date, Pertinent Papers, etc.)

Examiner Initial	Copies Enclosed	Document Description
W	X	"Atomic Layer Deposition (ALD 2002) Conference, August 19-21, 2002, at Hanyang University in Seoul, Korea," Conference Schedule [online] [retrieved 2003-07-08]. Retrieved from the Internet:<URL: http://www.av.org/conferences/ald/2002/program/aug19.html>; 3 pgs.
W	X	"Atomic Layer Deposition (ALD 2002) Conference, August 19-21, 2002, at Hanyang University in Seoul, Korea," Oral and slide Presentations [CD-ROM]. Available online from the Internet:<URL: https://www.av.org/conferences/ald/2002/cd_form.html>: 2 CDs.

EXAMINER

Date Considered

*Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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	Information Disclosure Statement mailed: July 12, 2004	

Examiner Initials	Copies Enclosed	Document Description
	X	Gordon et al., "Vapor deposition of metal oxides and silicates: possible gate insulators for future microelectronics," <i>Chem. Mater.</i> , 2001, 13(8):2463-4.
		Hawley, <i>The Condensed Chemical Dictionary</i> , 10 th Edition, Van Nostrand Reinhold Co., New York, 1981; 225-226.
	X	Hendrix et al., "Composition control of $\text{Jf}_{1-x}\text{Si}_x\text{O}_2$ films deposited on Si by chemical-vapor deposition using amide precursors," <i>Appl. Phys. Lett.</i> , 2002, Apr. 1; 80(13):2362-4.
	X	Lee et al., "High-k gate dielectric applications using ALD Hf-based oxides," <i>Solid State Technology</i> , 2003, Jan.; 46(1): 45-6, 56.
	X	Liu et al., "Atomic Layer Deposition of Hafnium Oxide Thin Films from Tetrakis(dimethylamino)Hafnium (TDMAH) and Ozone," <i>Mat Res Soc Symp Proc</i> , 2003; 765:97-102.
	X	Maruyama et al., "Silicon dioxide thin films prepared by chemical vapor deposition from tetrakis (dimethylamino) silane and ozone," <i>Appl. Phys. Lett.</i> , 1993, Aug. 2; 63(5):611-13.
	X	Ohshita et al., "HfO ₂ growth by low-pressure chemical vapor deposition using the Hf(N(C ₂ H ₅) ₂) ₄ /O ₂ gas system," <i>Journal of Crystal Growth</i> , 2001; 233:292-7.
	X	Ohshita et al., "Using tetrakis-diethylamido-hafnium for HfO ₂ thin-film growth in low-pressure chemical vapor deposition," <i>Thin Solid Films</i> , 2002; 406:215-18.
	X	Ritala et al., "Atomic layer deposition of oxide thin films with metal alkoxides as oxygen sources," <i>Science</i> , 2000, Apr. 14; 288:319-21.
	X	Suzuki et al., "Atomic Layer Deposition of HfO ₂ using Hf(N(C ₂ H ₅) ₂) ₄ and O ₃ ," Poster Presentation, <i>ALD 2002 Conference</i> , Hanyang University, Seoul, 2002, Aug. 19; 14 pages.
		Vaartstra et al., "Syntheses and Structures of a Series of Very Low Coordinate Barium Compounds: Ba[N(SiMe ₃) ₂] ₂ (THF) ₂ , {Ba[N(SiMe ₃) ₂] ₂ (THF)} ₂ , and {Ba[N(SiMe ₃) ₂] ₂ } ₂ , <i>Inorg. Chem.</i> , 1991; 30:121-5.
		Vehkämäki et al., "Growth of SrTiO ₃ and BaTiO ₃ Thin Films by Atomic Layer Deposition," <i>Electrochemical and Solid-State Letters</i> , 1999; 2(10):504-6.

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	Applicant(s): Vaartstra et al.	Confirmation No.: 4467
	Application Filing Date: April 21, 2004	Group: 2812
	Information Disclosure Statement mailed:	October 18, 2004

U.S. PATENT DOCUMENTS

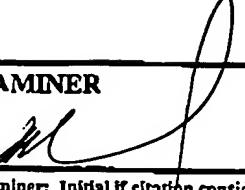
Examiner Initial	Copy Enclosed	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
69		US 2003/0188682	10/09/03	Tois et al.			
W		US 2004/0096582	05/20/04	Wang et al.			

FOREIGN PATENT DOCUMENTS

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							Yes	No

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